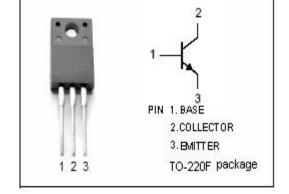


isc Silicon NPN Power Transistor

DESCRIPTION

- · Collector-Emitter Breakdown Voltage-
- : V_{(BR)CEO}= 50V(Min)
- · Low Collector Saturation Voltage-
 - : V_{CE(sat)}= 0.4V(Max.)
- · Wide Area of Safe Operation
- Complement to Type 2SB1135
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

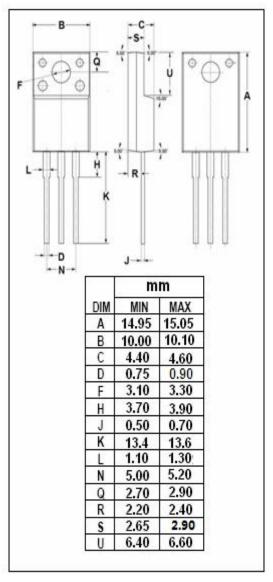


APPLICATIONS

• Designed for relay drivers, high speed inverters, converters and other general high current switching applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V_{CBO}	Collector-Base Voltage	60	V	
V _{CEO}	Collector-Emitter Voltage	50	V	
V _{EBO}	Emitter-Base Voltage	6	V	
Ic	Collector Current-Continuous	7	Α	
Ісм	Collector Current-Peak	12	А	
Pc	Collector Power Dissipation @T _a =25°C	2	W	
	Collector Power Dissipation @T _C =25 °C	25		
TJ	Junction Temperature 150		$^{\circ}$	
T _{stg}	T _{stg} Storage Temperature		℃	





isc Silicon NPN Power Transistor

2SD1668

ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
- STWIDOL	FANAMETER	CONDITIONS	IVIIIV	111.	WAX	ONI
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I_C = 1mA ; R_{BE} = ∞	50			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I _C = 1mA ; I _E = 0	60			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA ; I _C = 0	6			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 4A; I _B = 0.4A			0.4	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 40V ; I _E = 0			100	μА
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4V; I _C = 0			100	μА
h _{FE-1}	DC Current Gain	Ic= 1A; V _{CE} = 2V	70		280	
h _{FE-2}	DC Current Gain	I _C = 5A; V _{CE} = 2V	30			
f⊤	Current-Gain—Bandwidth Product	I _C = 1A; V _{CE} = 5V		10		MHz
Switching Times						
t _{on}	Turn-On Time			0.2		μ S
t _{stg}	Storage Time	$I_C = 2A, I_{B1} = I_{B2} = 0.2A;$ $R_L = 10 \Omega; V_{CC} = 20V$		0.9		μ S
t _f	Fall Time			0.3		μ S

♦ h_{FE-1} Classifications

Q	R	S
70-140	100-200	140-280

NOTICE:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.

isc website: www.iscsemi.com

isc & iscsemi is registered trademark